

MAXIMUM RATINGS

Rating	Symbol	BCY 78	BCY 79	Unit
Collector-Emitter Voltage	V _{CEO}	32	45	V _{dc}
Collector-Emitter Voltage (R _{BE} = 10 Ohms)	V _{CES}	32	45	V _{dc}
Emitter-Base Voltage	V _{EBO}	5		V _{dc}
Collector Current - Continuous	I _C	0.2		Amp
Total Device Dissipation @ T _A = 25°C	P _D	0.6	2.2B	Watt
Derate above 25°C				mW/°C
Total Device Dissipation @ T _C = 25°C	P _D	1		Watt
Derate above 25°C				mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	150	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	450	°C/W

**BCY78
BCY79**

**CASE 22-03, STYLE 1
TO-18 (TO-206AA)**

TRANSISTOR

PNP SILICON

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Type	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (I _C = 10 mA _{dc} , I _E = 0)	BCY78 BCY79	V _{(BR)CEO}	32 45			V _{dc}
Emitter-Base Breakdown Voltage (I _E = 2 μA _{dc} , I _C = 0)	all	V _{(BR)EBO}	5			V _{dc}
Collector Cutoff Current (V _{CE} = 32 V) (V _{CE} = 45 V) (V _{CE} = 32 V, T _A = 100°C, V _{BE} = 0.2 V) (V _{CE} = 45 V, T _A = 100°C, V _{BE} = 0.2 V) (V _{CE} = 25 V, T _A = 150°) (V _{CE} = 35 V, T _A = 150°)	BCY78 BCY79 BCY78 BCY79 BCY78 BCY79	I _{CES} I _{CEX} I _{CES}		0.2 0.2 0.2 0.5	100 100 20 20 10 10	nA μA _{dc} μA _{dc}
Emitter Base Cutoff Current (V _{EB} = 4 V)	all	I _{EBO}			20	nA

ON CHARACTERISTICS

DC Current Gain (I _C = 10 μA _{dc} , V _{CE} = 5 V _{dc}) (I _C = 2 mA _{dc} , V _{CE} = 5 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 1 V _{dc}) (I _C = 100 mA _{dc} , V _{CE} = 1 V _{dc})	BCY79-VII, BCY78-VII BCY79-VIII, BCY78-VIII BCY79-IX, BCY78-IX BCY79-X, BCY78-X BCY79-VII, BCY78-VII BCY79-VIII, BCY78-VIII BCY79-IX, BCY78-IX BCY79-X, BCY78-X BCY79-VII, BCY78-VII BCY79-VIII, BCY78-VIII BCY79-IX, BCY78-IX BCY79-X, BCY78-X BCY79-VII, BCY78-VII BCY79-VIII, BCY78-VIII BCY79-IX, BCY78-IX BCY79-X, BCY78-X BCY79-VII, BCY78-VII BCY79-VIII, BCY78-VIII BCY79-IX, BCY78-IX BCY79-X, BCY78-X	h _{FE}	30 40 100 120 180 250 380 80 120 160 240 40 45 60 60	145 220 300 170 250 350 500 190 260 380 550	220 310 460 630 400 630 1000		
Collector-Emitter Saturation Voltage (I _C = 100 mA _{dc} , I _B = 2.5 mA _{dc}) (I _C = 10 mA _{dc} , I _B = 0.25 mA)	all	V _{CE(sat)}	0.15 0.05	0.30 0.12	0.80 0.25	V _{dc}	
Base-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.25 mA) (I _C = 100 mA, I _B = 2.5 mA)	all	V _{BE(sat)}	0.6 0.75	0.70 0.90	0.85 1.2	V _{dc}	
Base-Emitter on Voltage (I _C = 2 mA _{dc} , V _{CE} = 5 V _{dc})	all	V _{BE(on)}	0.60	0.62	0.75	V _{dc}	

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Type	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$)	all	f_T	180	300		MHz
Output Capacitance ($V_{CE} = 10\text{ Vdc}$, $I_C = 0$, $f = 1\text{ MHz}$)	all	C_{ob}		3.5	7	pF
Input Capacitance ($V_{BE} = 0.5\text{ V}$, $I_C = 0$, $f = 1\text{ MHz}$)	all	C_{ib}		8	15	pF
Small Signal Current Gain ($I_C = 2\text{ mA}$, $V_{CE} = 5\text{ Vdc}$, $f = 1\text{ kHz}$)	BCY78-VII, BCY79-VII BCY78-VIII, BCY79-VIII BCY78-IX, BCY79-IX BCY78-X, BCY79-X	h_{fe} (h_{21e})		200 260 330 520		
Input Impedance ($I_C = 2\text{ mA}$, $V_{CE} = 5\text{ Vdc}$, $f = 1\text{ kHz}$)	BCY78-VII, BCY79-VII BCY78-VIII, BCY79-VIII BCY78-IX, BCY79-IX BCY78-X, BCY79-X	h_{ie} (h_{11e})	1.6 2.5 3.2 7.5		4.5 6 8.5 12	Kohms
Voltage Feedback Ratio ($I_C = 2\text{ mA}$, $V_{CE} = 5\text{ Vdc}$, $f = 1\text{ kHz}$)	BCY78-VII, BCY79-VII BCY78-VIII, BCY79-VIII BCY78-IX, BCY79-IX BCY78-X, BCY79-X	h_{re} (h_{12e})		1.5 2 2 3		$\times 10^{-4}$
Noise Figure ($I_C = 0.2\text{ mA}$, $V_{CE} = 5\text{ Vdc}$, $R_S = 2\text{ Kohms}$, $f = 1\text{ kHz}$)	all	NF		2	6	dB
SWITCHING CHARACTERISTICS						
$I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$, $I_{B2} = 1\text{ mA}$ $V_{BB} = 3.6\text{ V}$, $R_1 = R_2 = 5\text{ K}\Omega$ $R_L = 990\text{ ohms}$ * See test circuit.		t_d t_r t_{on}		35 50 85	150	nS
		t_s t_f t_{off}		400 80 480	800	
$I_C = 100\text{ mA}$, $I_{B1} = 10\text{ mA}$, $I_{B2} = 10\text{ mA}$ $V_{BB} = 5\text{ V}$, $R_1 = 500\ \Omega$, $R_2 = 700\ \Omega$ $R_L = 98\text{ ohms}$ * See test circuit.		t_d t_r t_{on}		5 50 55	150	nS
		t_s t_f t_{off}		250 200 450	800	

TEST CIRCUIT

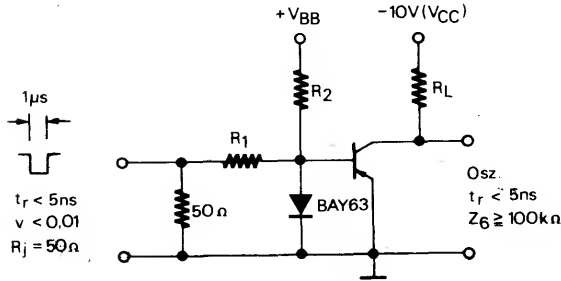


FIGURE 1 - CURRENT GAIN
(BCY78-VII/BCY79-VII)

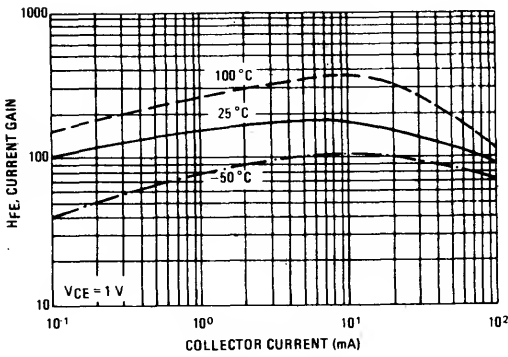


FIGURE 2 - CURRENT GAIN
(BCY78-VIII/BCY79-VIII)

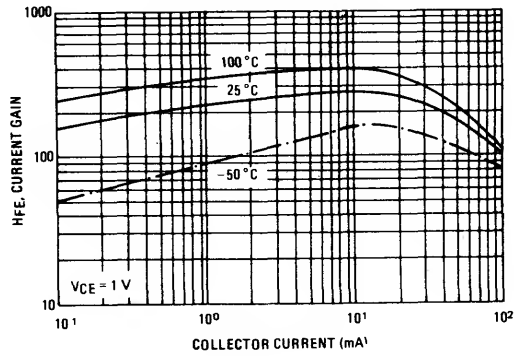


FIGURE 3 - CURRENT GAIN
(BCY78-IX/BCY79-IX)

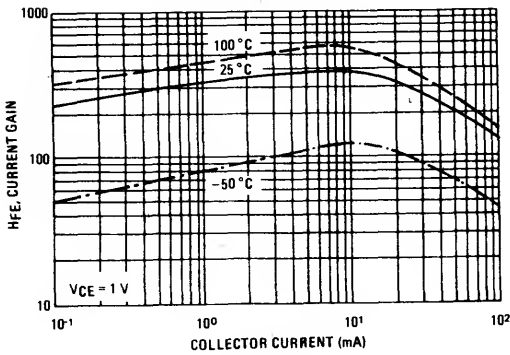
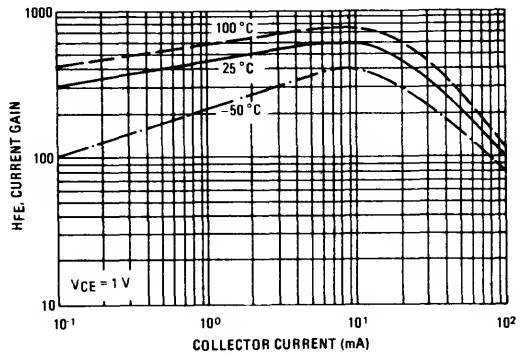


FIGURE 4 - CURRENT GAIN
(BCY78-X/BCY79-X)



BCY78, BCY79

FIGURE 5 – SATURATION VOLTAGE

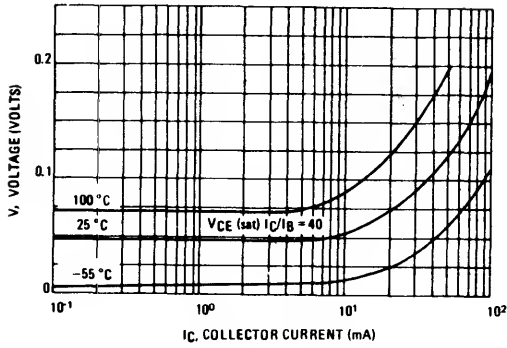


FIGURE 6 – SATURATION VOLTAGE

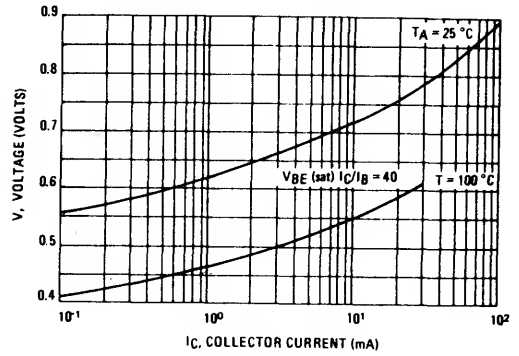


FIGURE 7 – INPUT CHARACTERISTIC (COMMON EMITTER CIRCUIT)

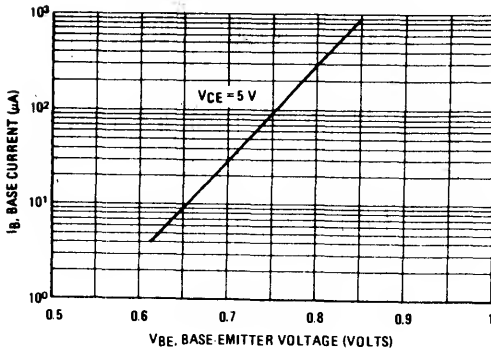


FIGURE 8 – TOTAL PERMISSIBLE POWER DISSIPATION (BCY78/BCY79)

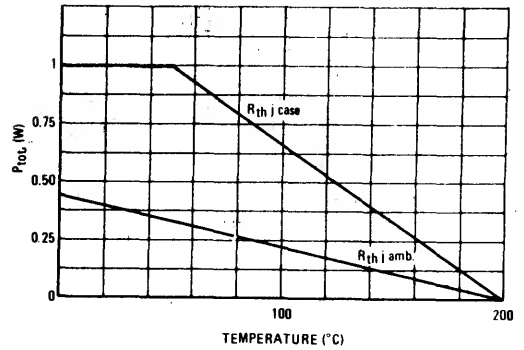


FIGURE 9 – CURRENT GAIN BANDWIDTH PRODUCT

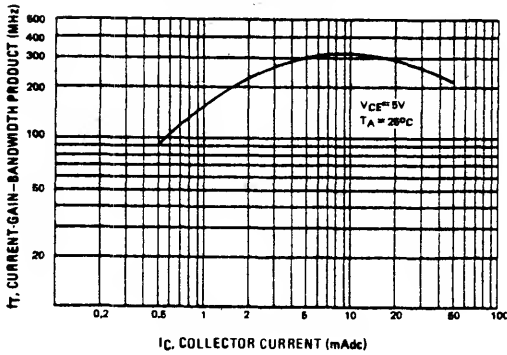
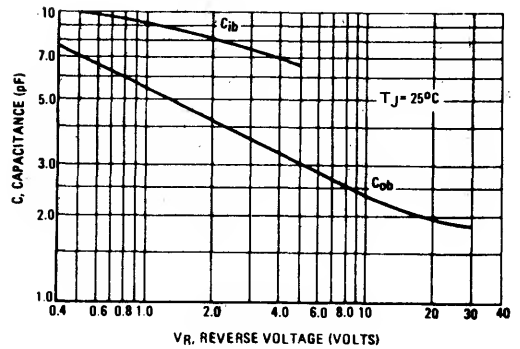


FIGURE 10 – CAPACITANCES



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